RoHS

COMPLIANT

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# N-Channel 80 V (D-S) MOSFET

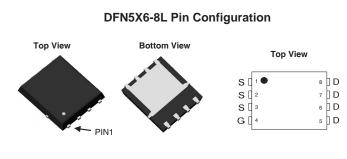
PRODUCT SUMMARY							
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ) (Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)				
80	6.1 at V <sub>GS</sub> = 10 V	85	109 nC				

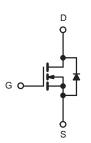
#### **FEATURES**

- DT-Trench Power MOSFET
- 100 % Rg and UIS tested
- Low on-resistance RDS(on)

### **APPLICATIONS**

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply





N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V <sub>DS</sub>	80	V			
Gate-Source Voltage	V <sub>GS</sub>	± 20	V			
Continuous Drain Current /T 450 °C\2	T <sub>C</sub> = 25 °C		85	А		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>C</sub> = 100 °C	I <sub>D</sub>	67			
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	280				
Single Avalanche Energy	E <sub>AS</sub>	430	mJ			
Mayimum Dayyar Dissipations	T <sub>C</sub> = 25 °C	В	110	W		
Maximum Power Dissipation <sup>c</sup>	T <sub>C</sub> = 100 °C	$P_{D}$	44			
Operating Junction and Storage Temperature R	T <sub>J</sub> , T <sub>stg</sub>	- 55 to +150	°C			

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) <sup>d</sup>	R <sub>thJA</sub>	45	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	1.15	] C/VV		

#### Notes

- $a. \ \ \, \text{Calculated continuous current based on maximum allowable junction temperature}.$
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>0JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	80	-	-	.,	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	-	4	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zone Oaks Walkers Buris O seed		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	1	- 1			
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 64 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	1	-	50	μA 50	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	85	-	-	Α	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	ı	6.1	7.8	mΩ	
Forward Transconductance a	9 <sub>fs</sub>	$V_{DS} = 5 \text{ V}, I_D = 20 \text{ A}$	-	50	-	S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		-	5040	-	pF	
Output Capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 40 V, f = 1 MHz	-	298	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	293	-		
Total Gate Charge <sup>c</sup>	$Q_g$		-	109	-	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 40 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	17	-		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	33.5	-		
Gate Resistance	$R_{g}$	f = 1 MHz	ı	1	-	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	11	-		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 40 \text{ V}, I_D = 20 \text{ A}, R_g = 3\Omega$	-	6.5	-		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	V <sub>GS</sub> = 10 V	-	25	-	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>		-	6.5	-		
<b>Drain-Source Body Diode Ratings and</b>	Characterist	ics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	85	А	
Pulsed Current	I <sub>SM</sub>		-	-	280	Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 V	ı	-	1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs	-	32	-	ns	
Reverse Recovery Charge	$Q_{rr}$	i <sub>F</sub> = 20 A, αί/αι = 100 ΑγμS	-	55	-	nC	

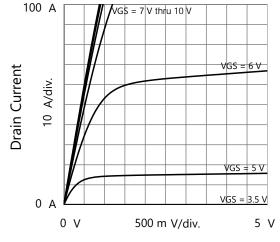
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

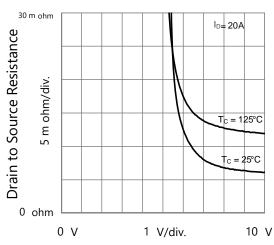
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



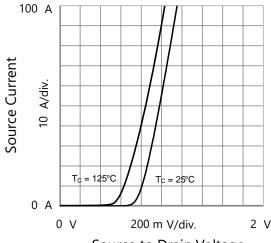
#### **TYPICAL CHARACTERISTICS** (T<sub>C</sub> = 25 °C, unless otherwise noted)



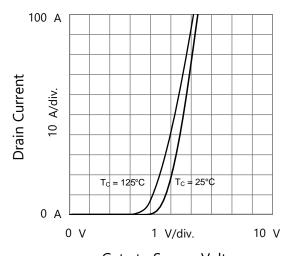
Drain to Source Voltage Output Characteristics



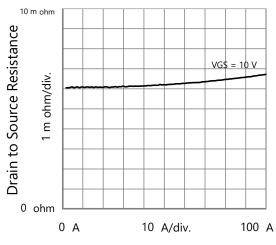
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



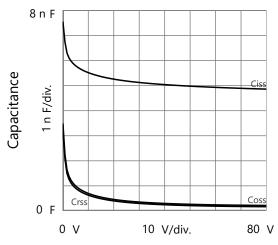
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics

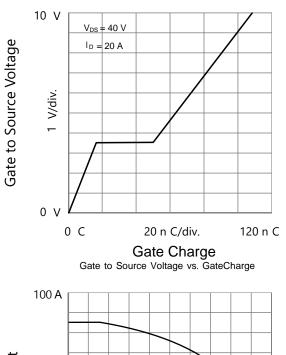


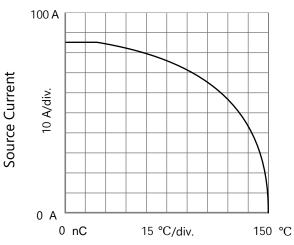
Drain Current



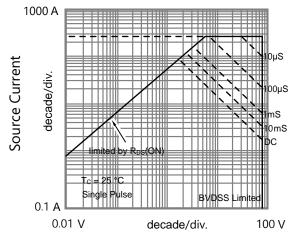
Drain to Source Voltage Capacitances

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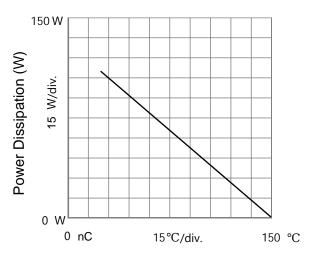




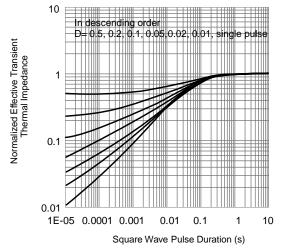
T<sub>C</sub> - Case Temperature



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



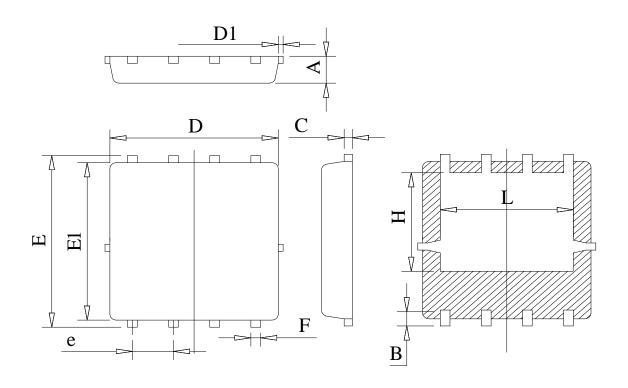




**Normalized Thermal Transient Impedance** 



### DFN5X6-8L PACKAGE OUTLINE



## **COMMON DIMENSIONS** (UNITS OF MEASURE=MILLIMETER)

Unit: mm

Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
C	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25

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